

# RBN40H125S1FPQ-A0

1250V - 40A - IGBT Power Switching

R07DS1380EJ0141 Rev.1.41 Oct.14.2021

### **Features**

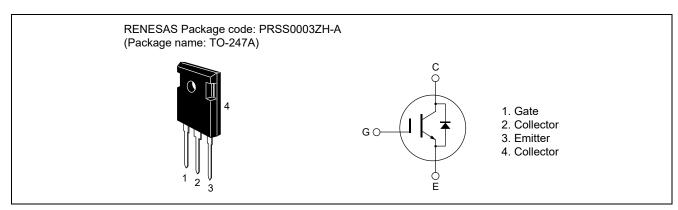
- Trench gate and thin wafer technology (G8H series)
- Built in fast recovery diode in one package
- Low collector to emitter saturation voltage
   V<sub>CE(sat)</sub> = 1.8 V typ. (at I<sub>C</sub> = 40 A, V<sub>GE</sub> = 15 V, Ta = 25°C)
- · Quality grade: Standard

- · High speed switching
- Short circuit withstands time (10 µs min.)
- Applications: UPS, Welding, photovoltaic inverters, Power converter system

### **Key Performance**

Туре	V <sub>CES</sub>	lc	V <sub>CE(sat)</sub> , T <sub>C</sub> =25°C	l <sub>F</sub>	tsc	Tj
RBN40H125S1FPQ-A0	1250 V	40 A	1.8 V	25 A	10μs	175 °C

### **Outline**



## **Absolute Maximum Ratings**

 $(Tc = 25^{\circ}C)$ 

Item		Symbol	Ratings	Unit
Collector to emitter voltage		V <sub>CES</sub>	1250	V
Gate to emitter voltage		V <sub>GES</sub>	±30	V
Collector current	Tc = 25 °C	Ic	80	Α
	Tc = 100 °C	Ic	40	Α
Collector peak current		I <sub>C(peak)</sub> Notes1	160	Α
Diode forward current	Tc = 25 °C	lf	50	Α
	Tc = 100 °C	lf	25	Α
Diode forward peak current		I <sub>F(peak)</sub> Notes1	160	Α
Collector power dissipation		Pc Notes2	319	W
Junction temperature		T <sub>j</sub> Notes2	175	°C
Storage temperature		T <sub>stg</sub>	-55 to +150	°C

Note: Continuous heavy condition (e.g. high temperature/voltage/current or high variation of temperature) may affect a reliability even if it is within the absolute maximum ratings. Please consider derating condition for appropriate reliability in reference Renesas Semiconductor Reliability Handbook (Recommendation for Handling and Usage of Semiconductor Devices) and individual reliability data.

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Please use this device in the thermal conditions which the junction temperature does not exceed 175 °C. Renesas IGBT Application Note is disclosed about reliability test and application condition up to 175 °C.

### **Thermal Resistance Characteristics**

 $(Tc = 25^{\circ}C)$ 

Item	Symbol	Max. Value Notes3	Unit
Junction to case thermal resistance (IGBT)	R <sub>th(j-c)</sub>	0.47	°C/W
Junction to case thermal resistance (Diode)	R <sub>th(j-c)</sub>	1.61	°C/W

Notes: 3. Designed target value on Renesas measurement condition. (Not tested)

## **Electrical Characteristics**

 $(Tc = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector to emitter leakage current	I <sub>CES</sub>	_	_	200	μА	V <sub>CE</sub> = 1250 V, V <sub>GE</sub> = 0 V
Gate to emitter leakage current	Iges	_	_	±1	μΑ	V <sub>GE</sub> = ±30 V, V <sub>CE</sub> = 0 V
Gate to emitter threshold voltage	V <sub>GE(th)</sub>	5.3	_	7.1	V	$V_{CE} = 10 \text{ V}, I_{C} = 1.3 \text{ mA}$
Collector to emitter saturation voltage	VcE(sat)	_	1.8	2.34	V	I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15V Notes4
Input capacitance	Cies	_	2330	_	pF	V <sub>CE</sub> = 25 V
Output capacitance	Coes	_	120	_	pF	V <sub>GE</sub> = 0 V
Reverse transfer capacitance	Cres	_	18	_	pF	f = 1 MHz
Total gate charge	Qg	1	85	_	nC	V <sub>GE</sub> = 15 V
Gate to emitter charge	Qge	_	25	_	nC	V <sub>CE</sub> = 600 V
Gate to collector charge	Qgc	_	44	_	nC	Ic = 40 A
Turn-on delay time	t <sub>d(on)</sub>	_	25	_	Ns	Vcc = 600 V
Rise time	tr	_	11	_	ns	V <sub>GE</sub> = 15 V/–15 V
Turn-off delay time	t <sub>d(off)</sub>	_	124	_	ns	Ic = 40 A
Fall time	tf		67	_	ns	$R_g = 10 \Omega$
Turn-on loss energy	Eon	_	2.0	_	mJ	Tc = 25 °C
Turn-off loss energy	E <sub>off</sub>	1	1.4	_	mJ	Inductive load Notes5
Total switching energy	E <sub>total</sub>	_	3.4	_	mJ	
Turn-on delay time	t <sub>d(on)</sub>	-	26	_	Ns	V <sub>CC</sub> = 600 V
Rise time	tr	_	13	_	ns	V <sub>GE</sub> = 15 V/–15 V
Turn-off delay time	t <sub>d(off)</sub>	1	152	_	ns	I <sub>C</sub> = 40 A
Fall time	t <sub>f</sub>	_	106	_	ns	$R_g = 10 \Omega$
Turn-on loss energy	Eon	1	3.3	_	mJ	Tc = 150 °C
Turn-off loss energy	E <sub>off</sub>	_	2.5	_	mJ	Inductive load Notes5
Total switching energy	Etotal	_	5.8	_	mJ	
Short circuit withstand time Notes6	tsc	10	_	_	μS	Vcc ≤ 720 V, VgE = 15 V
						Tc ≤ 150 °C
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Diode forward voltage	VF	_	2.8	3.64	V	I <sub>F</sub> = 25 A Notes4
Diode reverse recovery time	t <sub>rr</sub>		156	_	ns	$I_F = 25 \text{ A}, d_{iF}/d_t = 300 \text{ A}/\mu\text{s}$
Diode reverse recovery charge	Qrr	_	0.92	_	μC	

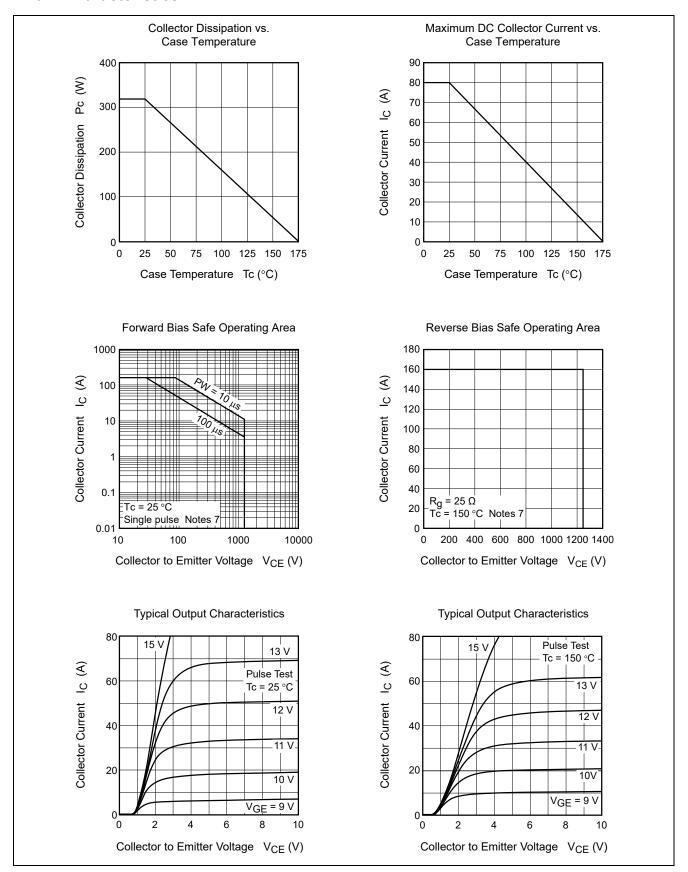
Notes: 4. Pulse test

Diode peak reverse recovery current

5. Switching time test circuit and waveform are shown below.

6. Designed target value on Renesas measurement condition. (Not tested)

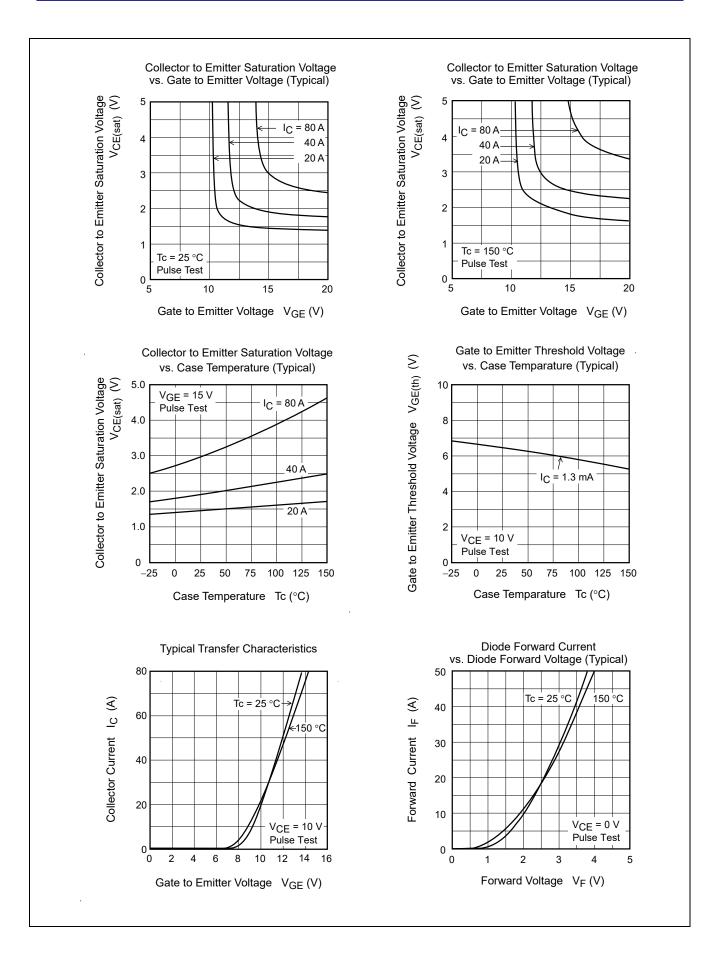
### **Main Characteristics**

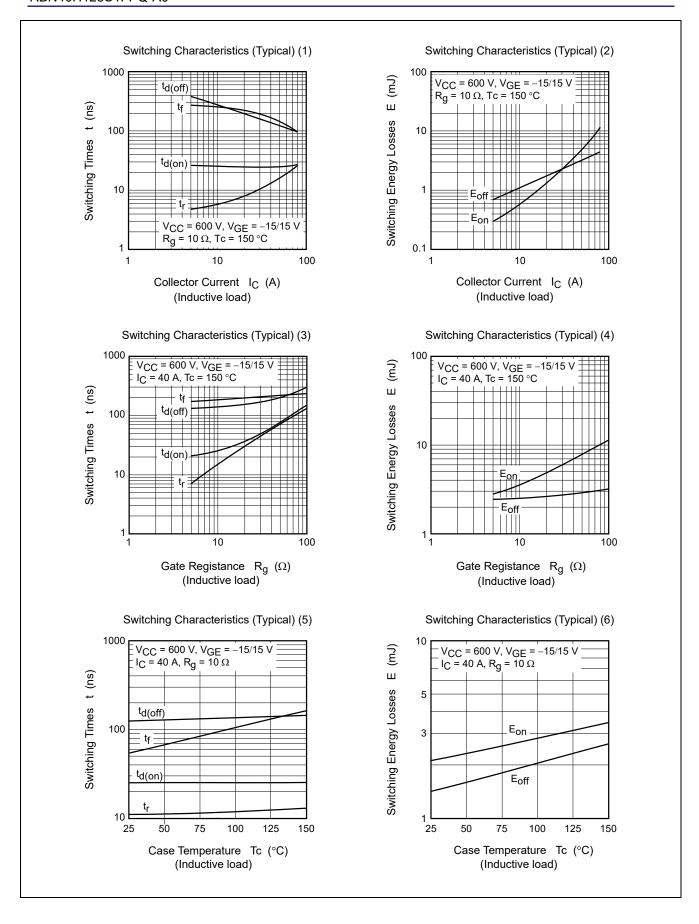


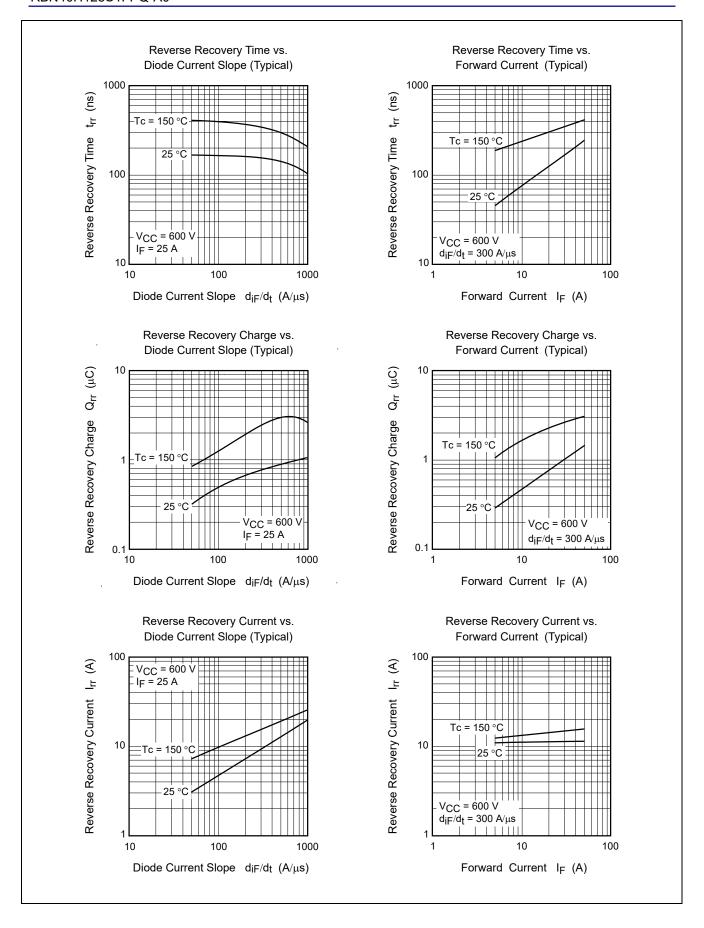
Notes: 7. Designed target value on Renesas measurement condition. (Not tested)

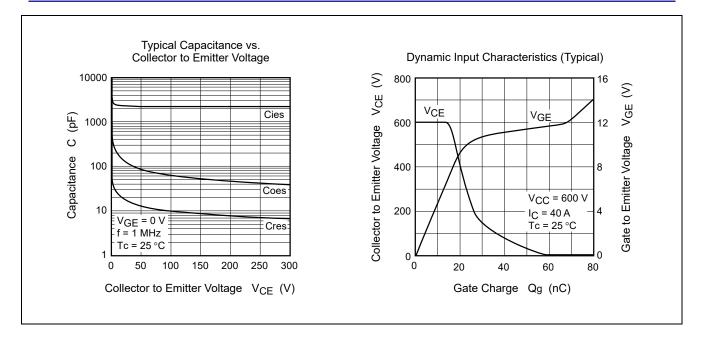
Renesas recommends that operating conditions are designed according to a document "Power MOS FET •

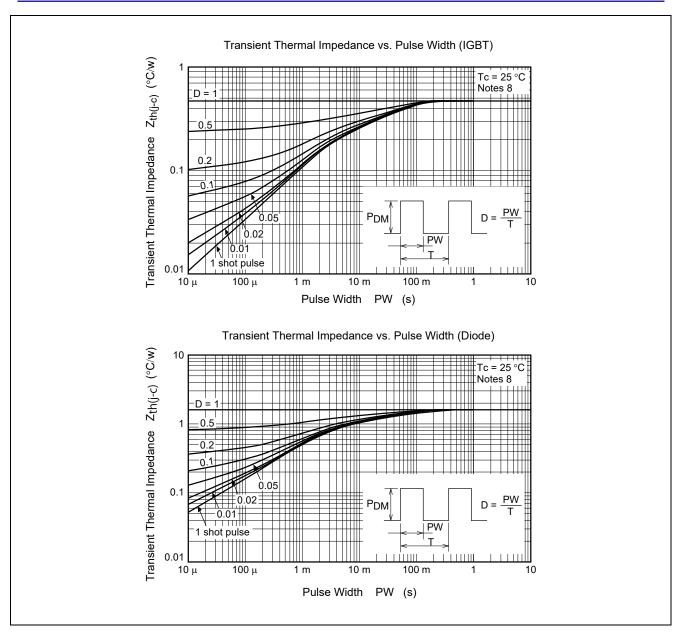
IGBT Attention of Handling Semiconductor Devices".



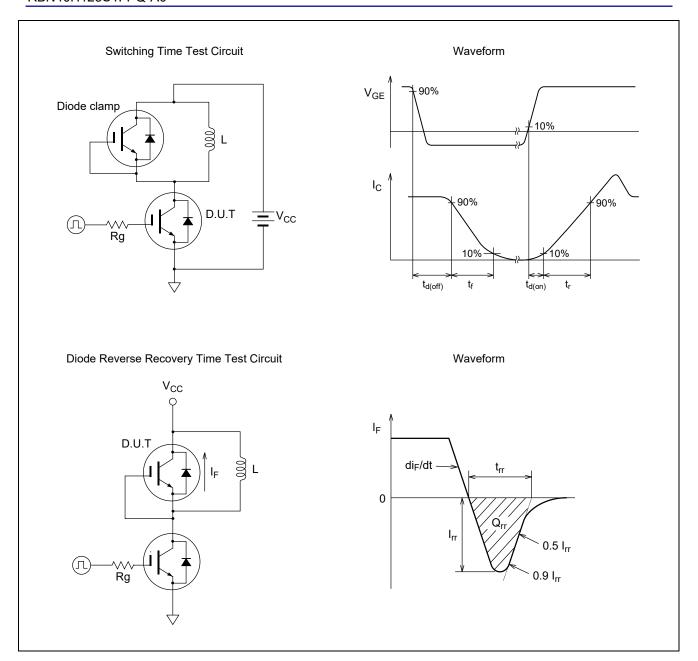




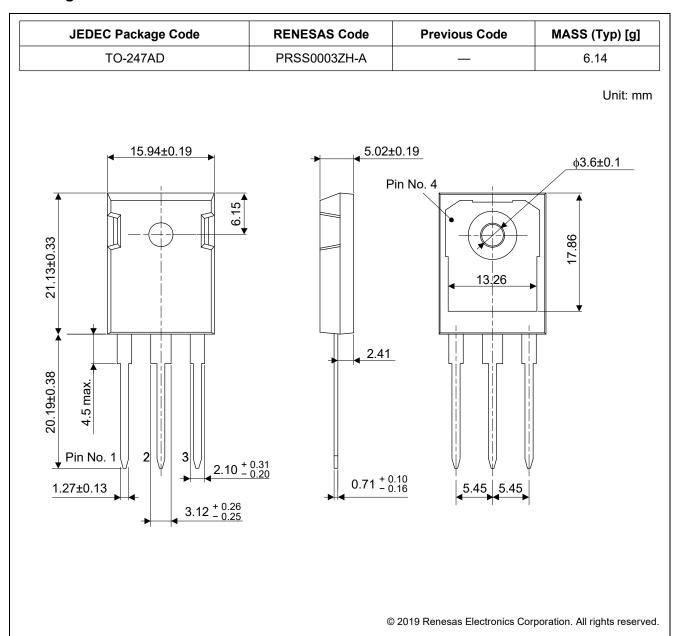




Notes: 8. Designed target value on Renesas measurement condition. (Not tested)



# **Package Dimensions**



# **Ordering Information**

Orderable Part Number	Quantity	Shipping Container		
RBN40H125S1FPQ-A0#CB0	240 pcs	Box (Tube)		

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